A	2020.11.26	ALL	BRCS80N03DP		

BRCS060N03ZB

Rev.A Nov.-2020

DATA SHEET

/ Descriptions

DFN 3*3A-8L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a DFN 3*3A-8L Plastic Package.

/ Features

V_{DS} (V) = 30V

I_D =40 A (V_{GS} = ±20V)

$R_{DS(ON)}$@10V≤6mR(Typ.4.7mR)

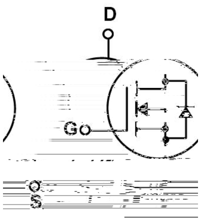
。HF Product.

/ Applications

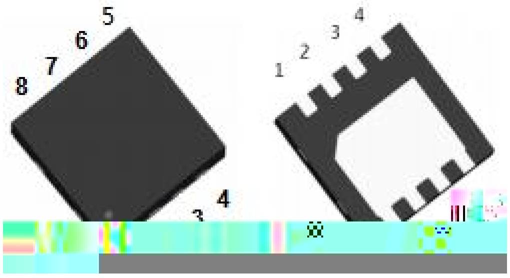
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



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/ Marking

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Drain Current		I_D(Tc=25℃)	40	A
Drain Current - Pulsed		I_{DM}	130	A
Gate-Source Voltage		V_{GSS}	±20	V
Single Pulsed Avalanche Energy		E_{AS}	211	mJ
Avalanche Current		I_{AS}	23	A
Power Dissipation		P_D(Tc=25℃)	29	W
Operating and Storage Temperature Range		T_J,T_{stg}	-55 to 150	
Junction-to-Ambient	t≤10	$R_{\theta JA}$	40	℃/W
Junction-to-Ambient	Steady-State		75	
Junction-to-Case	Steady-State	$R_{\theta JC}$	4.2	

BRCS060

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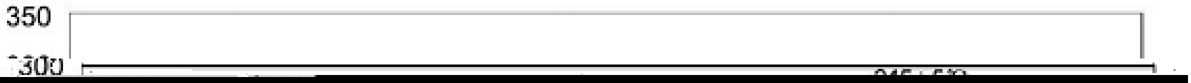

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	Note:
1 150 180 60 90sec;	1.Preheating:150~180℃, Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3 2 10℃/sec.	3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type !	Units " # $					Dimension " % & (unit ' mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
DFN 3*3A-8L	5,000	2	10,000	6	60,000	13″ ×12	360×360×50	380×335×366